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so what should i do? how can i fix this issue? Any help is appreciated. Thanks in advance. A: If you download the.rar file, try extracting it on a different computer. If you extract on a Windows machine, then it should be fine. The present invention relates to a method of forming a protective film in a semiconductor device. More particularly, the present invention relates to a method of forming a protective film with a metal oxide by a sputtering method. A metal oxide formed on a semiconductor device, such as gate insulating film and interlayer insulating film, is known to be advantageous as a protective film which prevents the diffusion of impurities and the corrosion of the metal. For example, Japanese Patent Publication No. 22995/1985 discloses a semiconductor device in which a metal oxide film having a thickness of less than 100 nm is formed on a semiconductor substrate to prevent the diffusion of impurities. Further, Japanese Patent Laid-open No. 59111/1984 discloses a semiconductor device in which a metal oxide film having a thickness of 10 to 200 nm is formed on an active region in order to prevent the corrosion of aluminum. In the formation of the protective film by the sputtering method, an argon ion or nitrogen ion is employed as a reactive gas. According to the Japanese Patent Laid-open No. 59111/1984, a layer of oxide is formed as a reaction product by the formation of the protective film on the gate electrodes. This oxide layer, however, absorbs moisture to corrode the gate electrodes. In order to prevent this phenomenon, a protective film is formed on the source and drain electrodes. The metal oxide film formed by a sputtering method contains a large quantity of oxygen and hence an oxygen partial pressure is preferably reduced to decrease the volume of the layer. Further, a temperature of the semiconductor substrate is preferably decreased to improve the crystallinity of the semiconductor substrate. If the temperature is set to about 300.degree. C., however, the bonding force of the oxide film formed by the sputtering method is remarkably decreased.Are You Preparing for a Baby Shower? Are you preparing for a baby

shower? If you've decided that you're going to throw a baby shower for your best friend, it's time to start thinking about planning. If you're the baby shower organizer, here are a few of the most important things to 6d1f23a050

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